

100mA40V LowVF(For Glass Seal)

Chip Information

Chip Size	0.45 x 0.45mm
Pad Size	0.27 x 0.27mm
Chip Quantity	54477 pcs/wafer
Scribe Line Width	40um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Ag Bump40um (For Glass Seal)
Chip Thickness/Back Metal : See below "Ordering Information"	

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	100	mA	
Peak Forward Surge Current	IFSM	1	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Test Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.550	0.530	0.430	V	IF=100mA Ta=25degC
	VF2	0.340	0.330	0.300	V	IF=10mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	100	50	2	uA	VR=40V Ta=25degC
	IR2	25000		1250	uA	VR=40V Ta=100deg
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV1	42	44	55	V	IR=80uA
	BV2	42	44	55	V	IR=500uA
	deltaBV	2.5	2		V	BV2-BV1
Junction Capacitance	Cj			6	pF	V=10V,f=1MHz
Reverse Recovery Time	trr			4	nS	IF=IR=10mA irr=1mA

Ordering Information

Chip Type	Chip Thickness	Back Metal
YHG08A	150 +/- 20um	Ti-Ni-Ag(For Glass Seal)

Note:
Designed For RB441Q